L Number	Hits	Search Text	DB	Time stamp
Number 2	20	((bipolar adj transistor) and (base with	USPAT;	2004/08/08
	20	((silicon Si) and ((silicon adj germanium)	US-PGPUB	14:16
		sige si-ge)) same depletion)) not		
		((bipolar adj transistor) and (base with		
		((silicon Si) and ((silicon adj germanium)		
3	19	sige si-ge)) with depletion)) (bipolar adj transistor) and (base with	USPAT;	2004/08/08
١		((silicon Si) and ((silicon adj germanium)	US-PGPUB	13:34
		sige si-ge)) with depletion)		
4	39		USPAT;	2004/08/08
		((silicon Si) and ((silicon adj germanium)	US-PGPUB	13:34
		sige si-ge)) same depletion)) not ((bipolar adj transistor) and (base with		
		((silicon Si) and ((silicon adj germanium)		
		sige si-ge)) with depletion))) or		
		((bipolar adj transistor) and (base with		
		((silicon Si)and ((silicon adj germanium) sige si-ge)) with depletion))		
1	166		USPAT;	2004/08/08
-		((non-saturated nonsaturated ((non "not")	US-PGPUB	14:32
		adj saturated)))		
5	33		USPAT;	2004/08/08
		((non-saturated nonsaturated ((non "not") adj saturated)))) and (438/\$.ccls. or	US-PGPUB	14:10
		257/\$.ccls.)		
6	7	(((bipolar adj transistor) and	USPAT;	2004/08/08
		((non-saturated nonsaturated ((non "not")	US-PGPUB	13:59
		adj saturated)))) and (438/\$.ccls. or		
7	2	257/\$.ccls.)) and (depletion) (("6762106") or ("5484737")).PN.	USPAT;	2004/08/08
	_	(()) 2 () 10 1/0 . , , , , , , , , , , , , , , , , , ,	US-PGPUB	14:10
8	0	(USPAT;	2004/08/08
		deplet\$	US-PGPUB	14:15
9	О	((("6762106") or ("5484737")).PN.) and	USPAT;	2004/08/08
		breakdown	US-PGPUB	14:15
10		///HC7C010CH) /H5404727H)		0004/00/00
10	0	((("6762106") or ("5484737")).PN.) and boltage	USPAT; US-PGPUB	2004/08/08
-		Dozougo	05 10105	*****
11	1	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/08/08
		voltage	US-PGPUB	14:15
12	1	((("6762106") or ("5484737")).PN.) and	USPAT;	2004/08/08
	_	voltage	US-PGPUB	14:15
13	192	((bipolar adj transistor) and (base with thickness with breakdown))	USPAT; US-PGPUB	2004/08/08
14	o		USPAT;	2004/08/08
		thickness with breakdown))) not basis	US-PGPUB	14:32
15	0	(((- F	USPAT;	2004/08/08
17	0	thickness with breakdown)) not "basis"	US-PGPUB	14:32
1 ′	"	((bipolar adj transistor) and ((non-saturated nonsaturated ((non "not")	USPAT; US-PGPUB	2004/08/08 14:32
		adj saturated)))) and (((bipolar adj		
		transistor) and (base with thickness with		
16	139	breakdown))	IICDATE-	2004/08/08
10	139	thickness with breakdown)) not "basis"	USPAT; US-PGPUB	16:19
18	42	((((bipolar adj transistor) and (base	USPAT;	2004/08/08
		with thickness with breakdown))) not	US-PGPUB	14:34
19	1	"basis") and (thickness near2 base) ("5484737").PN.	IIGDAT.	2004/08/08
10		\ J3U3/J/ /.EN.	USPAT; US-PGPUB	15:24
20	0	(("5484737").PN.) and (mis misfet)	USPAT;	2004/08/08
21		//#5404707#\ pyr \	US-PGPUB	15:24
21	0	(("5484737").PN.) and (mis misfet)	USPAT; US-PGPUB	2004/08/08
22	1	(("5484737").PN.) and (transistor)	USPAT;	2004/08/08
	_	,,, ,, data (ozdiložio odž)	US-PGPUB	15:24

23	0	(("5484737").PN.) and (heterojunction)	USPAT;	2004/08/08
			US-PGPUB	15:30
25	300	bipolar with mis	USPAT;	2004/08/08
			US-PGPUB	15:52
26	16	(bipolar with (misfet mis)) same	USPAT;	2004/08/08
		advantage	US-PGPUB	15:53
27	4	1	USPAT;	2004/08/08
1 - '	_	thickness with breakdown with optimiz\$))	US-PGPUB	16:22
28	7	((bipolar adj transistor) and (base with	USPAT;	2004/08/08
20	1	thickness with optimiz\$) same breakdown)	US-PGPUB	16:29
29	5	(((bipolar adj transistor) and (base with	USPAT;	2004/08/08
29			US-PGPUB	16:30
20	1 14	thickness) same optimiz\$) same breakdown)		1
30	14		USPAT;	2004/08/08
1	_	thickness) same optimiz\$) same breakdown)	US-PGPUB	16:30
31	7	(((bipolar adj transistor) and ((base	USPAT;	2004/08/08
i	-	with thickness) same optimiz\$) same	US-PGPUB	16:31
		breakdown)) not (((bipolar adj		
		transistor) and (base with thickness with		
		optimiz\$) same breakdown))		
32	136	((((bipolar adj transistor) and (base	USPAT;	2004/08/08
		with thickness with breakdown))) not	US-PGPUB	16:33
		"basis") not (@ad>20030812 or		
		@rlad>20030812)		
33	128	((((bipolar adj transistor) and (base	USPAT;	2004/08/08
1	120	with thickness with breakdown))) not	US-PGPUB	16:33
1		"basis") not (@ad>20020815 or	00 10100	-0.55
1		Basis		
_	3	(("5323032") or ("5323031") or	USPAT;	2004/08/07
-	, ,		US-PGPUB	
	24006	("6365479")).PN.		14:24
-	34006	bipolar adj transistor	USPAT;	2004/08/07
			US-PGPUB	14:24
-	406	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		(silicon and (silicon adj germanium)))	US-PGPUB	18:33
-	92	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		(silicon and (silicon adj germanium))	US-PGPUB	18:41
		with (two second))		i
-	102	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		(silicon and (silicon adj germanium))	US-PGPUB	18:13
		with (two second double stacked))		
-	177	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		(silicon and (silicon adj germanium) (si	US-PGPUB	15:30
		and sige)) with (two second double	05 10105	10.00
		stacked))		
1_	82	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
1		("si/sige"))	US-PGPUB	15:56
1_	8	("S1/S1ge")) (bipolar adi transistor) and (base with		
	1 8	(bipolar adj transistor) and (base with ("si/sige/si"))	USPAT;	2004/08/07
1_	1		US-PGPUB	16:06
1 -	1	("5798277").PN.	USPAT;	2004/08/07
1	-	//UEZ0007ZU\ PM \}	US-PGPUB	15:30
-] 1	(("5798277").PN.) and emitter	USPAT;	2004/08/07
			US-PGPUB	15:31
-	84	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
	İ	("si/sige")) or (base with ("si/si-ge"))	US-PGPUB	15:57
-	82	((bipolar adj transistor) and (base with	USPAT;	2004/08/07
		("si/sige")) or (base with ("si/si-ge")))	US-PGPUB	19:04
		not (@ad>20030812 or @rlad>20030812)		
-	1	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		("si/si-ge/si"))	US-PGPUB	16:46
-	7		USPAT	2004/08/07
		"5440152" "5719415" "5798539"		16:27
	ĺ	"6031256").PN.		
-	1	09/252908	USPAT;	2004/08/07
1	l • -	, = 	US-PGPUB	16:46
I _	98	((bipolar adj transistor) and (base with	USPAT;	2004/08/07
	, , ,	(silicon and (silicon adj germanium))	US-PGPUB	17:07
		with (two second double stacked))) not	US-FGFUD	17.07
1				
1		((bipolar adj transistor) and (base with		
L	L	("si/sige")) or (base with ("si/si-ge")))		

-	97		USPAT;	2004/08/08
		(silicon and (silicon adj germanium))	US-PGPUB	16:33
		with (two second double stacked))) not		
		((bipolar adj transistor) and (base with		
		("si/sige")) or (base with		
		("si/si-ge")))) not (@ad>20030812 or		
		@rlad>20030812)		0004400407
-	1	("6346452").PN.	USPAT;	2004/08/07
		//#C24C4E0#\\ PX \\	US-PGPUB	17:50
-	0	(("6346452").PN.) and emitter	USPAT;	2004/08/07
	,	10/620401	US-PGPUB	17:50
-	1	10/638401	USPAT;	2004/08/07
	,	10/620401 1 -11 1	US-PGPUB	18:13
-	1	10/638401 and depletion	USPAT;	2004/08/07
	600	(1-4m-1-m-44 + h	US-PGPUB	18:13
-	689		USPAT;	2004/08/07
		((silicon Si)and ((silicon adj germanium)	US-PGPUB	18:34
1 _ i	10	sige si-ge)))	HCDAG -	2004/00/00
-	19	(bipolar adj transistor) and (base with	USPAT;	2004/08/08
		((silicon Si)and ((silicon adj germanium)	US-PGPUB	13:34
1_	39	sige si-ge)) with depletion)	HCD2m.	2004/00/07
-	39	(bipolar adj transistor) and (base with	USPAT;	2004/08/07
		((silicon Si)and ((silicon adj germanium)	US-PGPUB	18:51
_	20	sige si-ge)) same depletion)	HCDAM -	2004/09/02
-	20	((bipolar adj transistor) and (base with	USPAT;	2004/08/08
		((silicon Si) and ((silicon adj germanium)	US-PGPUB	13:34
		sige si-ge)) same depletion)) not		
		((bipolar adj transistor) and (base with		
		((silicon Si)and ((silicon adj germanium) sige si-ge)) with depletion))		
_	1	(bipolar adj transistor) and (base with	IICDAM.	2004/00/00
_	1	((silicon Si) and ((silicon adj	USPAT;	2004/08/08
		germanium) sige si-ge)) same	US-PGPUB	13:33
		((non-saturated nonsaturated ((non "not")		
		adj saturated))))		
_	75		USPAT;	2004/08/07
1	, 5	(silicon and (silicon adj germanium) (si	US-PGPUB	19:04
		and sige)) with (two second double	OD-FGFOD	19.04
		stacked))) not ((bipolar adj transistor)		
		and (base with (silicon and (silicon adj		
]	germanium)) with (two second double		
		stacked)))		
-	73	• • •	USPAT;	2004/08/07
		(silicon and (silicon adj germanium) (si	US-PGPUB	19:04
		and sige)) with (two second double		
		stacked))) not ((bipolar adj transistor)		
		and (base with (silicon and (silicon adj		
]		germanium)) with (two second double		
j i		stacked)))) not (@ad>20030812 or		
ļ		@rlad>20030812)		
-	51		USPAT;	2004/08/07
		with (silicon and (silicon adj germanium)	US-PGPUB	19:04
		(si and sige)) with (two second double		
	l	stacked))) not ((bipolar adj transistor)		
	l	and (base with (silicon and (silicon adj		
	l	germanium)) with (two second double		
	l	stacked)))) not (@ad>20030812 or		
	ľ	@rlad>20030812)) not (((bipolar adj		
		transistor) and (base with ("si/sige"))		
	-	or (base with ("si/si-ge"))) not		
		(@ad>20030812 or @rlad>20030812))		

-	51		USPAT;	2004/08/07
		with (silicon and (silicon adj germanium)	US-PGPUB	19:11
		(si and sige)) with (two second double		
		stacked))) not ((bipolar adj transistor)		
		and (base with (silicon and (silicon adj		
		germanium)) with (two second double		
	ĺ	stacked)))) not (@ad>20030812 or		
	1	@rlad>20030812)) not (((bipolar adj		
	İ	transistor) and (base with ("si/sige"))		
		or (base with ("si/si-ge"))) not		
		(@ad>20030812 or @rlad>20030812))) not		
		((bipolar adj transistor) and (base with		
	_	("si/sige/si")))		
-	3	hirofumi near kawai	USPAT;	2004/08/07
	L		US-PGPUB	19:11